

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

TK10A80E, ITK10A80E

• FEATURES

- Low drain-source on-resistance: R⊳s(on) ≤1.0Ω.
- Enhancement mode:

Vth = 2.5 to4.0V (V_{DS} = 10 V, I_D=1.0mA)

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

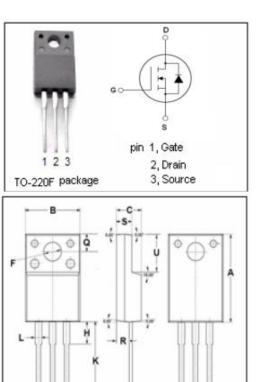
Switching Voltage Regulators

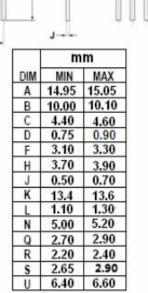
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	800	V			
V _{GS}	Gate-Source Voltage	±30	V			
ID	Drain Current-Continuous	10	А			
I _{DM}	Drain Current-Single Pulsed	30	А			
PD	Total Dissipation @T _c =25°C	50	W			
Tj	Max. Operating Junction Temperature	150	°C			
T _{stg}	Storage Temperature	-55~150	°C			

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	2.5	°C/W
Rth(ch-a)	th(ch-a) Channel-to-ambient thermal resistance		°C /W





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ELECTRICAL CHARACTERISTICS

 $T_{\text{C}}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	800			v
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = 10V; I _D =1.0mA	2.5		4.0	V
$R_{\text{DS(on)}}$	Drain-Source On-Resistance	V _{GS} =10V; I _D =5A			1000	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} =0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =640V; V _{GS} = 0V			10	μA
VSDF	Diode forward voltage	I _{DR} =10A, V _{GS} = 0 V			1.7	V

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